

**IN THE UNITED STATES  
PATENT AND TRADEMARK OFFICE**

**Patent Application**

**Inventors(s):** John Michael Hergenrother  
Pranav Kalavade

**Case:** 10-2

**Serial No.:**

**Filing Date:**

**Examiner:** H. Jey Tsai (in the parent)      **Group Art Unit:** 2812 (in the parent)

**Title:** Ultra Thin Body Vertical Replacement Gate MOSFET

**THE COMMISSIONER OF PATENTS AND TRADEMARKS  
WASHINGTON, DC 20231**

**SIR:**

**PRELIMINARY AMENDMENT**

No Office action has been received in the above-identified application, which is being concurrently filed herewith. Please amend the application as follows:

**IN THE SPECIFICATION**

Page 1, change the title from "Ultra Thin Body Vertical Replacement Gate MOSFET" to -- Method of Making Ultra Thin Body Vertical Replacement Gate MOSFET --.

**R e m a r k s**

The title has been changed to reflect the process nature of the claims retained in this divisional application.

No new matter has been added.

If during the consideration of this amendment and these remarks, the Examiner believes that prosecution will be advanced by further discussion, he is urged to contact the undersigned attorney at 610-691-7710 (voice) or 610-691-8434 (fax).

Respectfully,

By 

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Date: 08/26/03